



Bipolar NPN Bare Die – BTN152

Part Description

The BTN152 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Amplifier applications.

Key Parameters:

- VCBO = 120V
- VCEO = 120V
- VEBO = 5V
- hFE = 180-560 @ VCE = 6V, IC = 0.002A
- VCE(Sat) = 0.5V @ IC = 0.05A, IB = 5mA
- fT = 140 MHz @ VCE = 12V, IE = 0A
- COBO = 3pF @ VCB = 12V

Features

Low VCE(sat). Designed to provide performance equivalent to ROHM 2SC3906K

Die Size (Unawn)

450µm X 450µm, 18 Mils X 18 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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